**Product data sheet** 

## 1. General description

Hyperfast power diode in a SOD113 (2-lead TO-220F) plastic package.

### 2. Features and benefits

- Fast switching
- Isolated plastic package
- Low leakage current
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET

## 3. Applications

- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>RRM</sub>	repetitive peak reverse voltage			-	-	600	V
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; T <sub>h</sub> ≤ 75 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3		-	-	8	Α
Static characte	eristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 8 A; T <sub>j</sub> = 125 °C; <u>Fig. 6</u>		-	1.5	1.9	V
Dynamic characteristics							
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 200 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; Fig. 7		-	12	18	ns





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# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	K — A
2	Α	anode		001aaa020
mb	n.c.	mounting base; isolated	TO-220F (SOD113)	

# 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BYC8X-600P	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113			

## 7. Marking

Table 4. Marking codes

Type number	Marking code
BYC8X-600P	BYC8X-600P

# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	600	V
$V_{RWM}$	crest working reverse voltage		-	600	V
$V_R$	reverse voltage	DC	-	600	V
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; T <sub>h</sub> ≤ 75 °C; square-wave pulse; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	8	А
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; $t_p$ = 25 $\mu$ s; $T_h \le$ 75 °C; squarewave pulse	-	16	А

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Symbol	Parameter	Conditions	Min	Max	Unit
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	91	Α
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	100	А
T <sub>stg</sub>	storage temperature		-65	175	°C
T <sub>j</sub>	junction temperature		-	175	°C

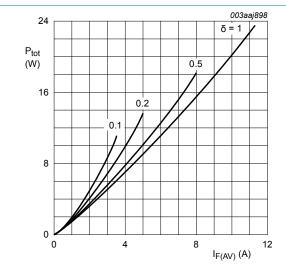


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

$$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$$
  
 $V_O = 1.581 \text{ V}; \text{ R}_S = 0.043 \Omega$ 

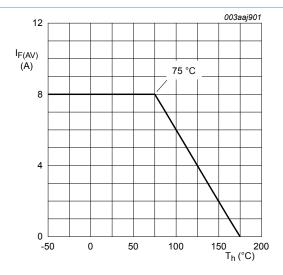


Fig. 3. Average forward current as a function of heatsink temperature; maximum values

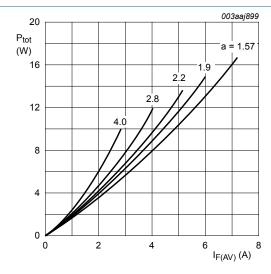


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

a = form factor = 
$$I_{F(RMS)}/I_{F(AV)}$$
  
 $V_O = 1.581 \text{ V}; R_S = 0.043 \Omega$ 

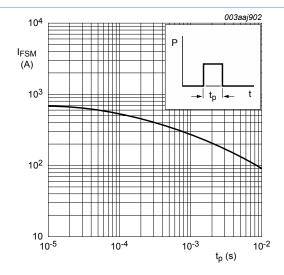


Fig. 4. Non-repetitive peak forward current as a function of pulse width; square waveform; maximum values

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## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-h)</sub>	thermal resistance from junction to heatsink	without heatsink compound	-	-	7.2	K/W
		with heatsink compound ; Fig. 5	-	-	5.5	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air		-	60	-	K/W

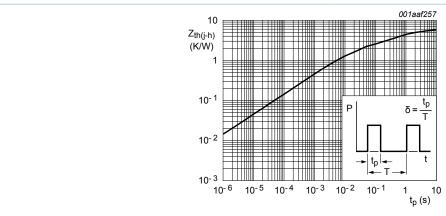


Fig. 5. Transient thermal impedance from junction to heatsink as a function of pulse width

### 10. Isolation characteristics

Table 7. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>isol(RMS)</sub>	RMS isolation voltage	50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C <sub>isol</sub>	isolation capacitance	f = 1 MHz ; from cathode to external heatsink	-	10	-	pF

## 11. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static characteristics							
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 8 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		-	-	3.4	V
		I <sub>F</sub> = 8 A; T <sub>j</sub> = 125 °C; <u>Fig. 6</u>		-	1.5	1.9	V
		I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C		-	1.4	-	V

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>R</sub>	reverse current	V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C	-	-	20	μA
		V <sub>R</sub> = 600 V; T <sub>j</sub> = 125 °C	-	-	200	μA
Dynamic ch	aracteristics					
Q <sub>r</sub>	recovered charge	$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	17	-	nC
		$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; \underline{\text{Fig. 7}}$	-	90	-	nC
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 200 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; Fig. 7	-	12	18	ns
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	19	-	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	2.2	A
		$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	-	6	A

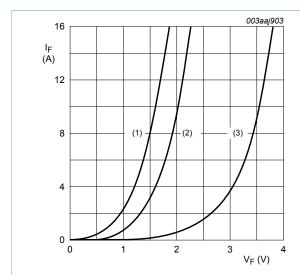


Fig. 6. Forward current as a function of forward voltage

(1)  $T_j = 125$  °C; typical values; (2)  $T_j = 125$  °C; maximum values; (3)  $T_j = 25$  °C; maximum values;  $V_O = 1.581$  V;  $R_S = 0.043$   $\Omega$ 

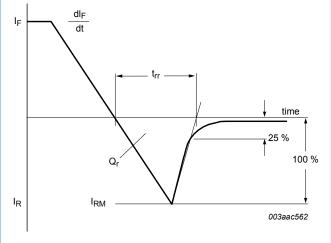


Fig. 7. Reverse recovery definitions; ramp recovery

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## 12. Package outline

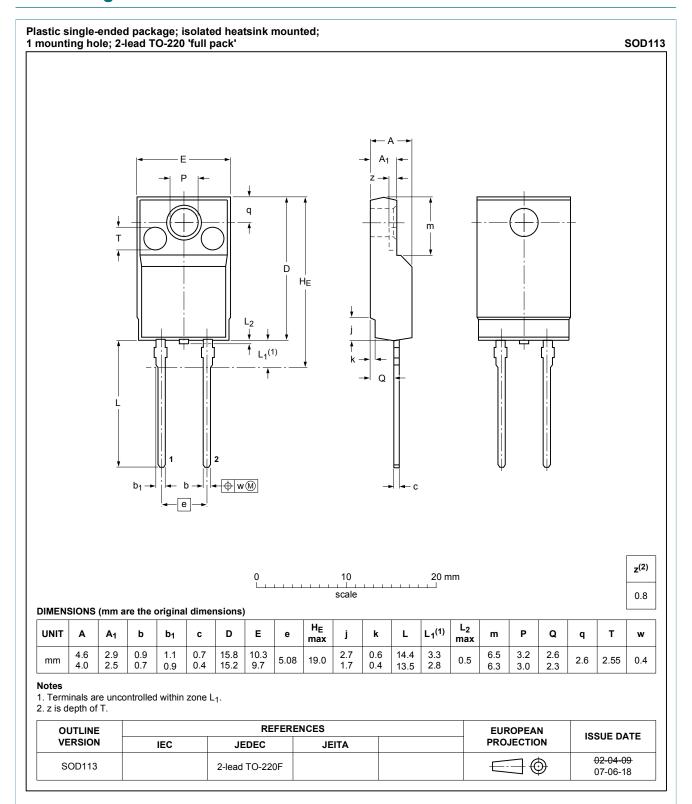


Fig. 8. Package outline TO-220F (SOD113)

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#### Hyperfast power diode

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#### 13.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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